
2SC5470

Silicon NPN Triple Diffused
Character Display Horizontal Deflection Output

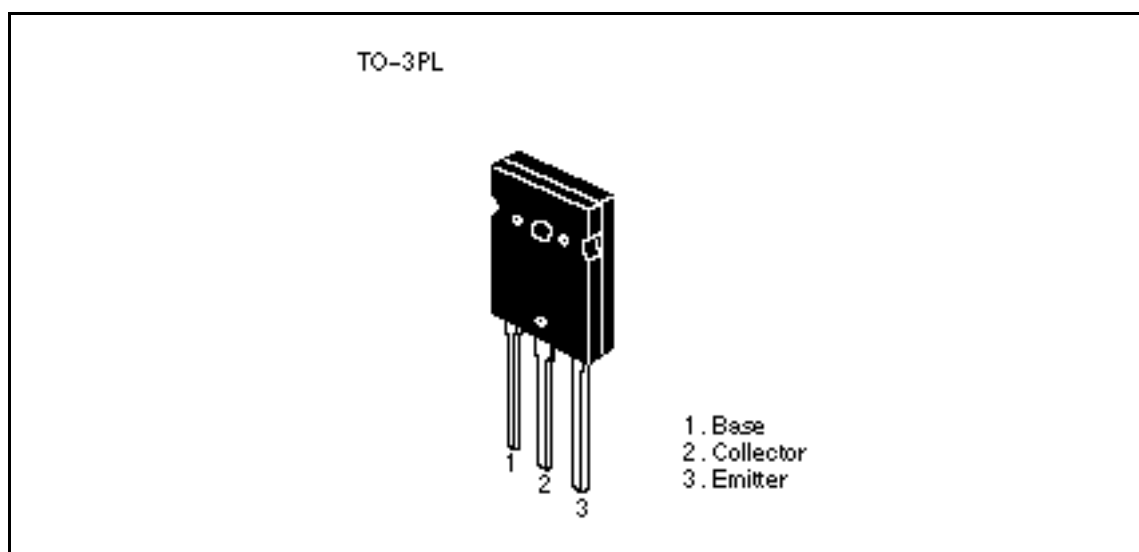
HITACHI

3rd. Edition
December 1997
Target Specification

Features

- High breakdown voltage
 $V_{CBO} = 1500 \text{ V}$
- High speed switching
 $t_f = 0.15 \text{ } \mu\text{sec}$ (typ.) at $f_H = 64\text{kHz}$

Outline



2SC5470

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1500	V
Collector to emitter voltage	V_{CEO}	700	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	20	A
Collector peak current	$i_{c(peak)}$	40	A
Collector power dissipation	P_C ^{Note1}	150	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

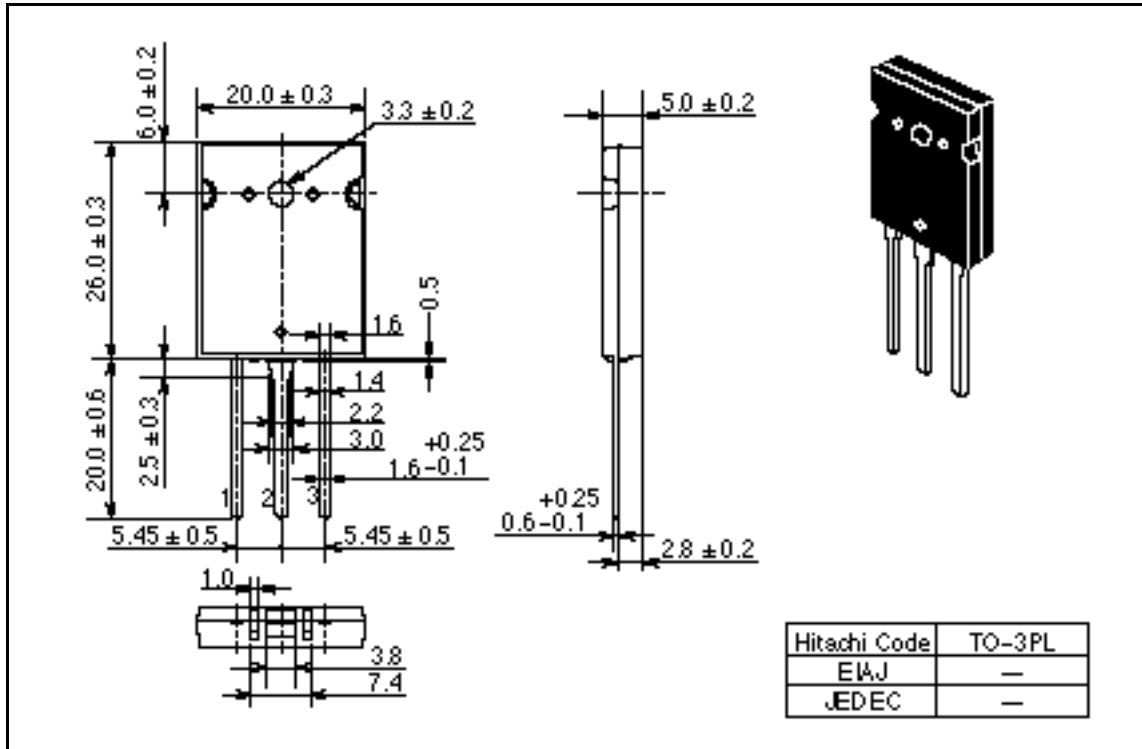
Note: 1. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	700	—	—	V	$I_C = 10\text{mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10\text{mA}$, $I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500\text{V}$, $R_{BE} = 0$
DC current transfer ratio	h_{FE1}	10	—	40		$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$
DC current transfer ratio	h_{FE2}	3.5	—	6.5		$V_{CE} = 5\text{V}$, $I_C = 10\text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 12\text{A}$, $I_B = 4\text{A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 12\text{A}$, $I_B = 4\text{A}$
Fall time	t_f	—	0.2	0.4	μs	$I_{CP} = 8\text{A}$, $I_{B1} = 3\text{A}$ $f_H = 31.5\text{kHz}$
Fall time	t_f	—	0.15	—	μs	$I_{CP} = 8\text{A}$, $I_{B1} = 2\text{A}$ $f_H = 64\text{kHz}$

Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohia-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brea, CA, 94005-4935

U.S.A.

Tel 415-589-8300

Fax 415-589-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Dornacher Straße 3

D-85632 Feldkirchen

München

Tel 089-9 91 80-0

Fax 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

Midlehead

Berkshire SL6 5YA

United Kingdom

Tel 0628-585000

Fax 0628-778322

Hitachi Asia Pte. Ltd.

#6 Collyer Quay #20-00

Hitachi Tower

Singapore 0404

Tel 535-2100

Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 706, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074

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